The following page (in construction) describes the simulation of devices with open boundary conditions such as RTDs with the nextnano.NEGF software.

Note that in the current version (2020-06-18), only single band calculations are supported for such open boundary conditions.

Simulation of devices with open boundary conditions

In order to simulate a system with open boundary conditions (instead of the default field-periodic boundary condition), contacts have to be defined by adding a <Contacts> section in the input file:

In this section, the carrier densities in the left and right contact have to been defined using the <DensityLeft> and <DensityRight> commands, as shown above. The unit is cm\$^{-3}\$.

The material of the left and right contacts needs to be defined by te command <MaterialLeft> and <MaterialRight>. The string value has to be an alias defined in the <Materials> section of the input file.

A broadening energy can be defined by the command <Broadening>. Indeed, scattering is not accounted in the contact, so that this commands allows a phenomenological broadening of the density of states in the contact.

The command <Ballistic> can be used to calculate ballistic transport between the contacts (i.e. no scattering process considered if its value is set to yes.

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